

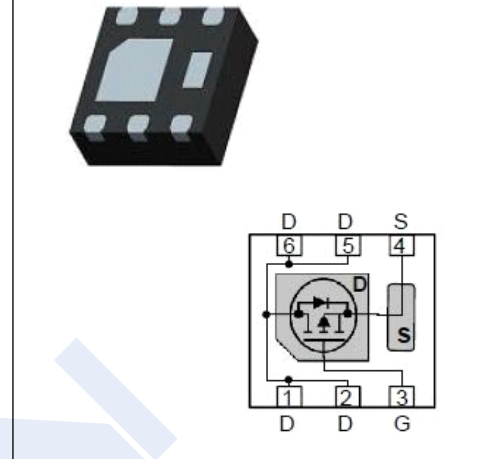
## P-Channel MOSFET

### KI005PDFN

#### ■ Features

- $V_{DS} (V) = -20V$
- $I_D = -4.1 A (V_{GS} = -4.5V)$
- $R_{DS(ON)} < 45m\Omega (V_{GS} = -4.5V)$
- $R_{DS(ON)} < 60m\Omega (V_{GS} = -2.5V)$

DFN2X2-06L



#### ■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	-20	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	
Continuous Drain Current	$I_D$	-4.1	A
Power Dissipation	$P_D$	1.4	W
Junction Temperature	$T_J$	150	$^\circ C$
Junction Storage Temperature Range	$T_{stg}$	-55 to 150	

#### ■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{DSS}$	$I_D = -250 \mu A, V_{GS} = 0V$	-20			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -20V, V_{GS} = 0V$			-1	$\mu A$
Gate-Body leakage current	$I_{GSS}$	$V_{DS} = 0V, V_{GS} = \pm 12V$			$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250 \mu A$	-0.45		-1	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -4.1A$			45	$m\Omega$
		$V_{GS} = -2.5V, I_D = -3A$			60	
Diode Forward Voltage	$V_{SD}$	$I_S = -1A, V_{GS} = 0V$			-1.2	V

#### ■ Marking

Marking	05P

Package Outline Dimensions

